WHAT IS CLAIMED IS:

1. A display unit comprising:

an insulator film formed on a substrate;

a display electrode formed on said insulator film; and

an impurity-introduced layer, formed on the surface of said display electrode and the surface of said insulator film, containing an impurity element having high electronegativity.

2. The display unit according to claim 1, wherein said insulator film includes an insulator film containing an organic component.

3. The display unit according to claim 1, wherein said impurity element having high electronegativity includes fluorine.

4. The display unit according to claim 3, wherein said impurity-introduced layer is formed on the surface of said insulator film, and includes any of a fluoride layer of a silicon oxide film, a fluoride layer of a silicon nitride film and a fluoride layer of a silicon oxynitride film.

5. The display unit according to claim 3, wherein said impurity-introduced layer includes a first layer, formed on the surface of said display electrode, mainly composed of indium fluoride.

6. The display unit according to claim 5, further comprising a second layer, formed on said first layer, mainly composed of carbon fluoride.

7. A display unit comprising:

an insulator film formed on a substrate;

a display electrode formed on said insulator film; and

a first layer, formed on the surface of said display electrode, mainly composed of indium fluoride.

8. The display unit according to claim 7, further comprising a second layer, formed on said first layer, mainly composed of carbon fluoride.

9. A method of fabricating a display unit comprising steps of:

forming an insulator film on a substrate;

forming a display electrode on said insulator film;

and

introducing an impurity element having high electronegativity into at least a portion of said insulator film not covered with said display electrode after formation of said display electrode.

10. The method of fabricating a display unit according to claim 9, wherein

said step of introducing said impurity element includes a step of etching the surface of at least said portion of said insulator film not covered with said display electrode simultaneously with introduction of said impurity element.

11. The method of fabricating a display unit according to claim 9, wherein

said step of introducing said impurity element having high electronegativity includes a step of exposing at least said portion of said insulator film not covered with said display electrode to plasma containing said impurity element having high electronegativity.

12. The method of fabricating a display unit according to claim 9, wherein

said step of introducing said impurity element having

high electronegativity includes a step of exposing at least said portion of said insulator film not covered with said display electrode to a radical containing said impurity element having high electronegativity.

13. The method of fabricating a display unit according to claim 9, wherein

said step of introducing said impurity element having high electronegativity includes a step of exposing at least said portion of said insulator film not covered with said display electrode to gas containing said impurity element having high electronegativity.

14. The method of fabricating a display unit according to claim 9, wherein

said step of introducing said impurity element having high electronegativity includes a step of exposing at least said portion of said insulator film not covered with said display electrode to liquid containing said impurity element having high electronegativity.

15. The method of fabricating a display unit according to claim 9, wherein

said step of introducing said impurity element having high electronegativity includes a step of introducing ions

containing said impurity element having high electronegativity into at least said portion of said insulator film not covered with said display electrode.

16. The method of fabricating a display unit according to claim 9, wherein

said insulator film includes an insulator film containing an organic component.

17. The method of fabricating a display unit according to claim 9, wherein

said impurity element having high electronegativity includes fluorine.

18. The method of fabricating a display unit according to claim 17, wherein

said step of introducing said impurity element includes a step of forming any of a fluoride layer of a silicon oxide film, a fluoride layer of a silicon nitride film and a fluoride layer of a silicon oxynitride film on the surface of said insulator film by introducing said impurity element.

19. The method of fabricating a display unit according to claim 9, wherein

said step of introducing said impurity element having high electronegativity includes a step of introducing said impurity element having high electronegativity into both of said insulator film and said display electrode.

20. The method of fabricating a display unit according to claim 19, wherein

said step of introducing said impurity element having high electronegativity includes a step of fluorinating said display electrode thereby forming a first layer mainly composed of indium fluoride on the surface of said display electrode.

21. The method of fabricating a display unit according to claim 20, wherein

said step of fluorinating said display electrode includes a step of forming said first layer mainly composed of indium fluoride on the surface of said display electrode while forming a second layer mainly composed of carbon fluoride on said first layer by exposing the surface of said display electrode to plasma containing fluorine and carbon.

22. The method of fabricating a display unit according to claim 19, wherein

said step of introducing said impurity element having high electronegativity includes a step of depositing a first layer mainly composed of indium fluoride on said display electrode by sputtering.

23. A method of fabricating a display unit comprising steps of:

forming an insulator film on a substrate;

forming a display electrode on said insulator film; and

forming a layer containing fluorine on the surface of said display electrode.

24. The method of fabricating a display unit according to claim 23, wherein

said step of forming said layer containing fluorine includes a step of forming a first layer mainly composed of indium fluoride on the surface of said display electrode while forming a second layer mainly composed of carbon fluoride on said first layer by exposing the surface of said display electrode to plasma containing fluorine and carbon.

25. The method of fabricating a display unit according to claim 23, wherein

said step of forming said layer containing fluorine includes a step of depositing a first layer mainly composed of indium fluoride on said display electrode by sputtering.